

isc Silicon PNP Power Transistor

2SA818

DESCRIPTION

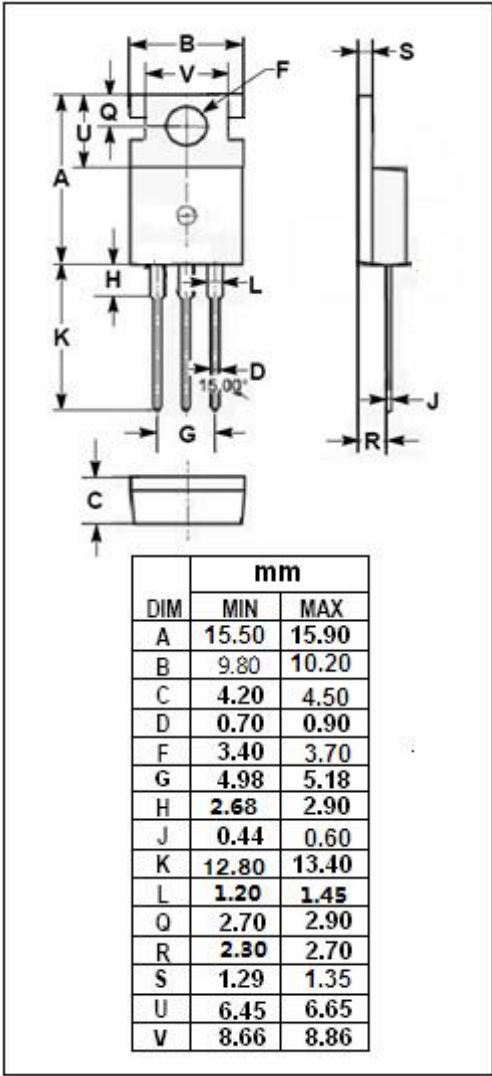
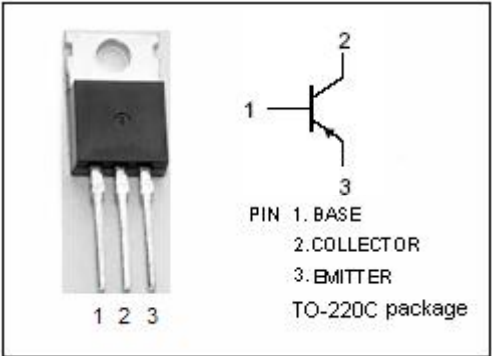
- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -160V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC1628

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-50	mA
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	1	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SA818****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A ; V _{CE} = -5V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -180V ; I _E = 0			-10.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-10.0	μ A
h _{FE}	DC Current Gain	I _C = -10mA ; V _{CE} = -5V	70		240	
f _T	Current-Gain—Bandwidth Product	I _C = -0.1A; V _{CE} = -5V		120		MHz